

Title (en)
Method of manufacturing a bonding substrate

Title (de)
Verfahren zur Herstellung eines verbundenden Substrates

Title (fr)
Procédé de fabrication d'un substrat collé

Publication
EP 0856876 A3 20000726 (EN)

Application
EP 98300615 A 19980128

Priority
JP 3279097 A 19970131

Abstract (en)
[origin: EP0856876A2] A method of manufacturing a bonding substrate is disclosed. An oxide film is formed on the surface of at least one of two semiconductor substrates, and the two substrates are brought into close contact with each other via the oxide film. The substrates are heat-treated in an oxidizing atmosphere in order to firmly join the substrates together. Subsequently, an unjoined portion at the periphery of a device-fabricating substrate is completely removed, and the thickness of the device-fabricating substrate is reduced to a desired thickness so as to yield a thin film. The surface of the thin film is then etched through vapor-phase etching in order to make the thickness of the thin film uniform. In the method, the oxide film on the unjoined portion of at least the support substrate is removed before the surface of the thin film is subjected to vapor-phase etching. The method prevents a groove from being formed in the surface of the unjoined portion (terrace portion) of the support substrate (base wafer) even when the surface of the thin film undergoes vapor phase etching. <IMAGE> <IMAGE>

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H01L 21/2007 (2013.01 - EP US)

Citation (search report)

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